



FEATURES

- Epitaxial planar die construction.
- Complementary PNP type available (MMBT3906-3L).
- Collector Current Capability $I_{CM} = 200\text{mA}$.
- Collector-emitter Voltage $V_{CEO}=40\text{V}$.
- MSL 1

APPLICATIONS

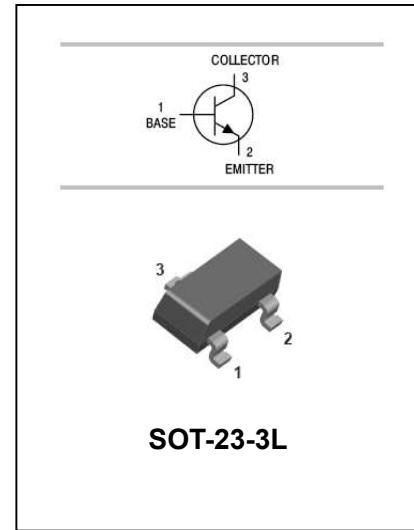
- General switching and amplification

ORDERING INFORMATION

| Type No. | Marking | Package Code |
|--------------|---------|--------------|
| MMBT3904□-3L | 1AM | SOT-23-3L |

□: none is for Lead Free package;

“G” is for Halogen Free package



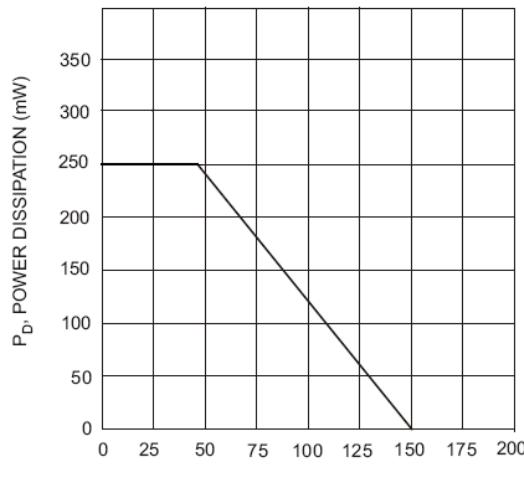
MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | Value | UNIT |
|-----------|-------------------------------|---------------------------------|-------------|------|
| V_{CBO} | collector-base voltage | open emitter | 60 | V |
| V_{CEO} | collector-emitter voltage | open base | 40 | V |
| V_{EBO} | emitter-base voltage | open collector | 6 | V |
| I_c | collector current (DC) | | 200 | mA |
| I_{CM} | peak collector current | | 200 | mA |
| I_{BM} | peak base current | | 100 | mA |
| P_{tot} | total power dissipation | $T_{amb} \leq 25^\circ\text{C}$ | 250 | mW |
| T_{stg} | storage temperature | | -65 to +150 | °C |
| T_j | junction temperature | | 150 | °C |
| T_{amb} | operating ambient temperature | | -65 to +150 | °C |

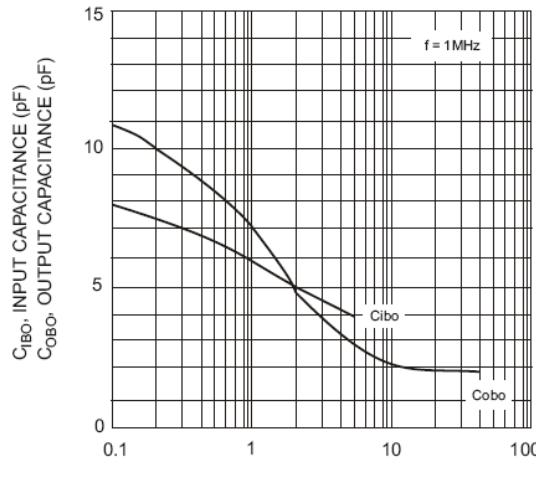

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|---|--------------------------------------|--|-----------------------------|-------------------------|-------------|
| I_{CBO} | collector cut-off current | $I_E = 0; V_{CB} = 30\text{ V}$ | - | 50 | nA |
| I_{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = 6\text{ V}$ | - | 50 | nA |
| h_{FE} | DC current gain | $V_{CE} = 1\text{ V};$ $I_C = 0.1\text{mA}$ $I_C = 1\text{mA}$ $I_C = 10\text{mA}$ $I_C = 50\text{mA}$ $I_C = 100\text{mA}$ | 60 80 100 60 30 | - - 300 - - | |
| $V_{CE(\text{sat})}$ | collector-emitter saturation voltage | $I_C = 10\text{mA}; I_B = 1\text{mA}$ | - | 200 | mV |
| | | $I_C = 50\text{mA}; I_B = 5\text{mA}$ | - | 300 | mV |
| $V_{BE(\text{sat})}$ | base-emitter saturation voltage | $I_C = 10\text{mA}; I_B = 1\text{mA}$ | 650 | 850 | mV |
| | | $I_C = 50\text{mA}; I_B = 5\text{mA}$ | - | 950 | mV |
| C_{obo} | Output Capacitance | $I_E = I_e = 0; V_{CB} = 5\text{V};$ $f = 1\text{MHz}$ | - | 4 | pF |
| C_{ibo} | Input Capacitance | $I_C = I_c = 0; V_{BE} = 500\text{mV};$ $f = 1\text{MHz}$ | - | 8 | pF |
| f_T | transition frequency | $I_C = 10\text{mA}; V_{CE} = 20\text{V};$ $f = 100\text{MHz}$ | 300 | - | MHz |
| F | noise figure | $I_C = 100\text{mA}; V_{CE} = 5\text{V};$ $R_S = 1\text{k}\Omega; f = 10\text{Hz to } 15.7\text{kHz}$ | - | 5 | dB |
| Switching times (between 10% and 90% levels); | | | | | |
| t_d | delay time | $I_{Con} = 10\text{mA}; I_{Bon} = 1\text{mA};$ $I_{Boff} = -1\text{mA}$ | - | 35 | ns |
| t_r | rise time | | - | 35 | ns |
| t_s | storage time | | - | 200 | ns |
| t_f | fall time | | - | 50 | ns |

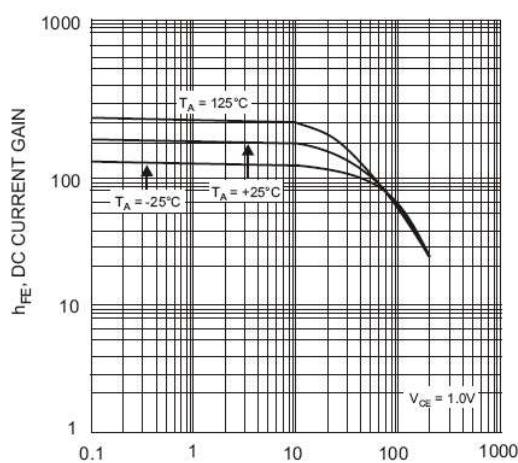
Note Pulse test: $tp \leq 300\text{ ms}$; $d \leq 0.02$.


TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified


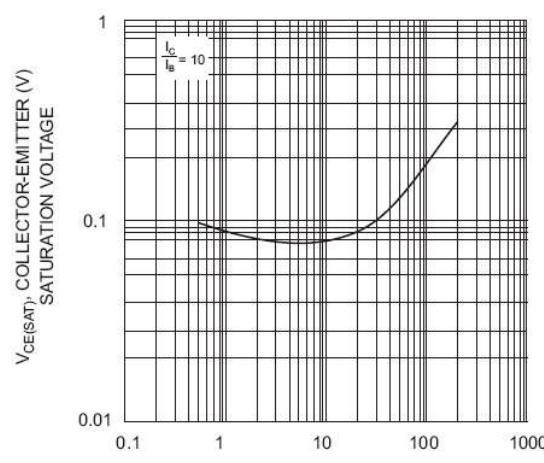
T_A , AMBIENT TEMPERATURE (°C)
Fig. 1, Max Power Dissipation vs
Ambient Temperature



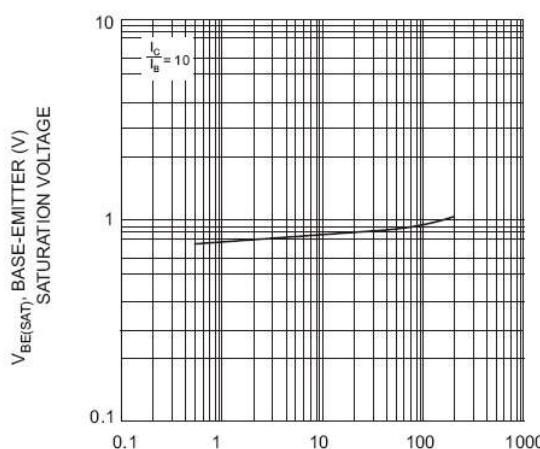
V_{CB} , COLLECTOR-BASE VOLTAGE (V)
Fig. 2, Input and Output Capacitance vs.
Collector-Base Voltage



I_C , COLLECTOR CURRENT (mA)
Fig. 3, Typical DC Current Gain vs
Collector Current



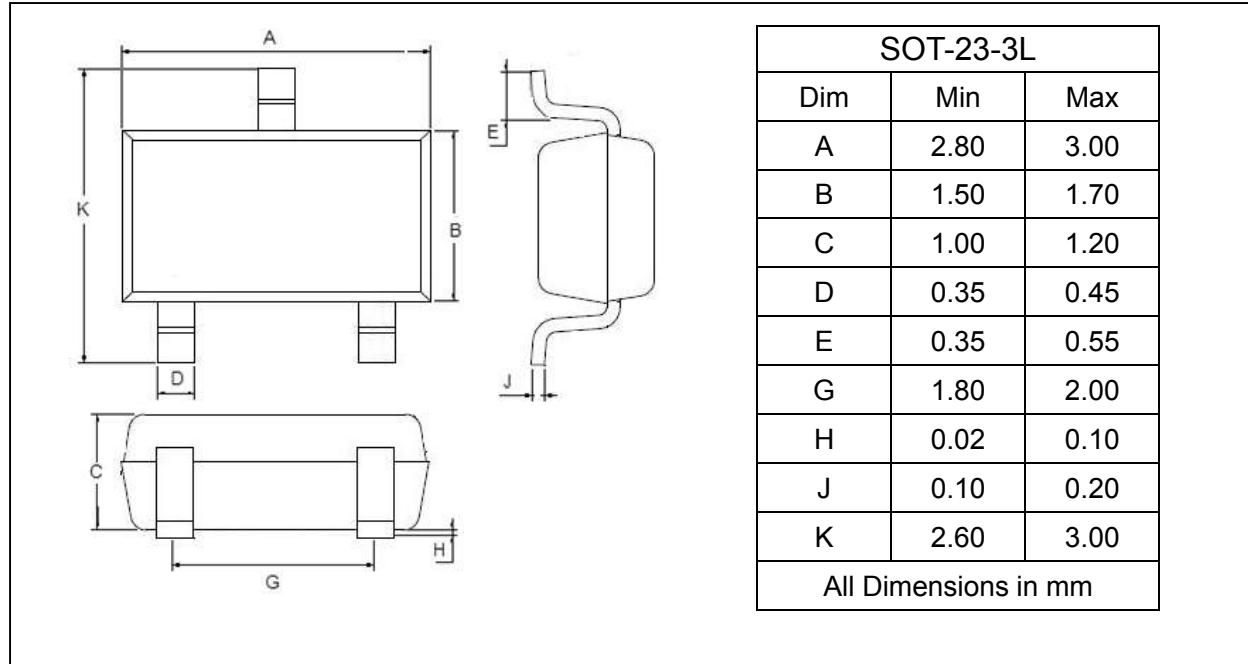
I_C , COLLECTOR CURRENT (mA)
Fig. 4, Typical Collector-Emitter
Saturation Voltage vs. Collector Current



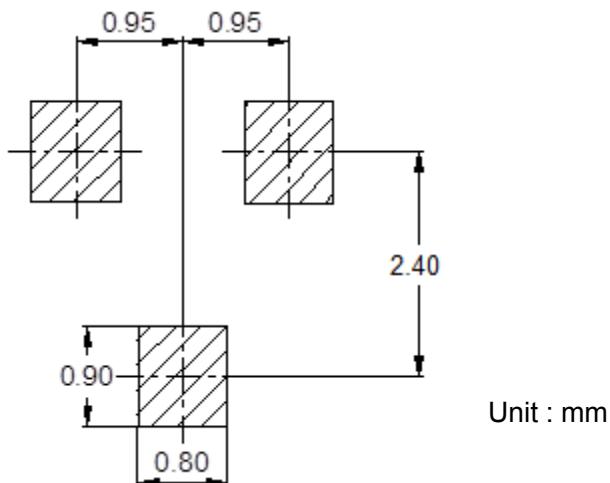
I_C , COLLECTOR CURRENT (mA)
Fig. 5, Typical Base-Emitter
Saturation Voltage vs. Collector Current



Plastic surface mounted package



SOLDERING FOOTPRINT



| Package | Reel | Reel Size | Box | Box Size(mm) | Carton | Carton Size(mm) |
|-----------|---------|-----------|-----------|--------------|------------|-----------------|
| SOT-23-3L | 3000pcs | 7inch | 45,000pcs | 203×203×195 | 180,000pcs | 438×438×220 |